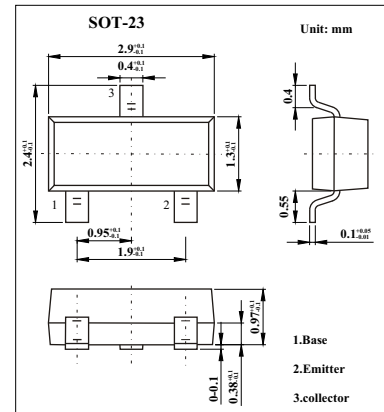


## NPN Silicon Transistor

### KST9018

#### Features

High current gain bandwidth product.  
power dissipation.(PC=200mW)



#### Absolute Maximum Ratings Ta = 25

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	30	V
Collector to Emitter Voltage	$V_{CEO}$	15	V
Emitter to Base Voltage	$V_{EBO}$	5	V
Collector Current to Continuous	$I_C$	50	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	
Storage Temperature	$T_{stg}$	-55 to 150	

#### Electrical Characteristics Ta = 25

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	30			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	15			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	5			V
Collector cut to off current	$I_{CBO}$	$V_{CB} = 12V, I_E = 0$			0.05	$\mu A$
Emitter cut to off current	$I_{EBO}$	$V_{EB} = 3V, I_C = 0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = 5V, I_C = 1mA$	70		190	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$			0.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 1mA$			1.4	V
Transition frequency	$f_T$	$V_{CE} = 5V, I_C = 5mA, f = 400MHz$	600			MHz

#### Marking

Marking	J8
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